## imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

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# PHOTONIC Silicon Photodiode, U.V. Enhanced Photoconductive DETECTORS INC. Type PDU-C113



PACKAGE DIMENSIONS INCH (mm) RED DOT INDICATES ANODE 0.140 [3.56] MAX .070 [1.78] 0.224 [5.69] 1.50 [38.1] MIN -WIRE ANODE BONDS PHOTODIODE 120° Ø0.265 [6.73 VIEWING 0.200 [5.08] ANGLE G Ø0.020 [0.51] OPTICAL EPOXY CATHODE CERAMIC 0.125 [3.18] SQUARE CERAMIC PACKAGE 0.113 [2.87] SQ ACTIVE AREA

ACTIVE AREA =  $7.95 \text{ mm}^2$ 

#### **APPLICATIONS**

- U.V. exposure meter
- Water purification
- Fluorescence
- U.V. A & B meters

## with a clear U.V. transmitting epoxy glob top.

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)							
SYMBOL	PARAMETER	MIN	MAX	UNITS			
VBR	Reverse Voltage		30	V			
T <sub>STG</sub>	Storage Temperature	-40	+100	с			
To	Operating Temperature Range	-40	+90	с			
Ts	Soldering Temperature*		+240	°C			
Ι	Light Current		500	mA			

DESCRIPTION

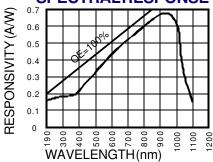
The PDU-C113 is a silicon, PIN planar

diffused, U.V. enhanced photodiode. Ideal

Packaged on a two lead ceramic substrate

for high speed photoconductive applications.





\*1/16 inch from case for 3 secs max

**FEATURES** 

High speed

Low capacitance

• U.V. enhanced

Low dark current

#### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS			
lsc	Short Circuit Current	H = 100 fc, 2850 K	90	110		μA			
ΙD	Dark Current	$H = 0, V_{R} = 5 V$		10	50	nA			
Rsh	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	100	250		MΩ			
TC RSH	RsH Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		% / °C			
CJ	Junction Capacitance	$H = 0, V_{R} = 5 V^{**}$		130		рF			
λrange	Spectral Application Range	Spot Scan	250		1100	nm			
R	Responsivity	$V_R = 0 V, \lambda = 254 nm$	.12	.18		A/W			
VBR	Breakdown Voltage	I = 10 µµA	15	25		V			
NEP	Noise Equivalent Power	V <sub>R</sub> = 5 V @ Peak		2.2x10 <sup>-14</sup>		W/ <del>/ Hz</del>			
tr	Response Time	$RL = 1 K\Omega V_R = 5 V$		58		nS			

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.\*\*f=1 MHz [FORM NO. 100-PDU-C113 REV A]